

Appl'n No.: 09/854,924

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ABSTRACT

A planar body of an oxide single crystal having a good crystallinity is grown stably to prevent cracks in the crystal, when the planar body of the oxide single crystal is grown with a μ pulling-down method. A raw material of the oxide single crystal is melted in a crucible 7. A seed crystal 15 is contacted to a melt 8. An oxide single crystal 31 is grown by pulling down the seed crystal 15 to draw the melt from an opening 13c of the crucible 7. A cooler is provided under the opening 13c of the crucible 7, which cools the oxide single crystal drawn from the opening of the crucible.

VERSION WITH MARKINGS TO SHOW CHANGES MADE
Amended abstract